

Notice of References Cited	Application/Control No. 10/618,478		Applicant(s)/Patent Under Reexamination KESHNER ET AL.	
	Examiner B. Chen		Art Unit 1762	Page 1 of 1

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	U	Watanabe, Takeshi et al., "Microwave-Excited Plasma CVD of a-Si:H Films Utilizing a Hydrogen Plasma Stream or by Direct Excitation of Silane". Japanese Journal of Applied Physics. Vol.26 (1987) pp.1215-1218. Part 1, No.8, 20 August 1987. ABSTRACT ONLY
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.